



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of)
Shunpei YAMAZAKI et al.) Art Unit: 2815
Application Serial No. 09/323,692) Examiner: Nguyen, D
Filed: June 2, 1999)
For: ELECTRO-OPTICAL DEVICE AND)
DRIVING METHOD FOR THE SAME)

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Amdt
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8-7-01

T. Flowers

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

Sir:

Responsive to the Office Action of February 28, 2001, the period for response having been extended two (2) months to July 28, 2001 (Saturday), the following amendments and remarks are submitted in connection with the above-identified application.

IN THE SPECIFICATION

Replace page 17, paragraph 1 with the following:

B1
After removing photoresist 27, the channel regions are then thermally annealed at 600°C for 10 to 50 hours in H₂ atmosphere to make active the impurities in the drain and source regions. An interlayer insulating film 37c of silicon oxide is deposited to a thickness of 0.2 to 0.6 μm by the same sputtering method as described above over the entire surface of the structure followed by etching by means of a photomask ⑤ for opening contact holes 39b through the interlayer film 37c and the oxide film 35 in order to provide accesses to the underlying source and drain regions 34b, 34a, 34b' and 34a'. The deposition of the interlayer insulating film 37c may be carried out by LPCVD, photo-CVD, ordinal pressure CVD (TEOS-ozone) . Next, an aluminum film of 0.5 to 1 μm thickness is deposited on the structure over the contact holes 39b and patterned to form source and drain electrodes 36b, 36a, 36b' and 36a' by means of a photomask ⑥ as illustrated in Fig.8 (F). An organic resin film 39 such as a transparent polyimide